

# Program at a Glance

		Room A (Monterosso, B1F)	Room B (Vernazza, 3F)	Room C (Forum 1, 3F)	Room D (Forum 2, 3F)	Lobby
<b>October 13 (SUN)</b>						
13:30–14:30	60'	[Short Course 1] Prof. Bernard Gil (CNRS–Univ. of Montpellier, France) "Current Status Regarding Discriminative Optical Properties of Various BN Polytypes"				Registration
14:30–15:30	60'	[Short Course 2] Prof. Dong–Pyo Han (Pukyong Nat'l Univ., Korea) "Small–Signal Analysis as a Useful Tool to Investigate the Nature of III–Nitride Semiconductor Light–Emitting Devices"				
15:30–15:50	20'	Coffee Break				
15:50–18:00	130'	[Short Course 3] Prof. Soon–Ku Hong (Chungnam Nat'l Univ., Korea) "Structural Defects in SiC Bulk and Epilayers"				
18:30–20:00	90'	Welcome Reception (Blue Seagull, 2F)				
<b>October 14 (MON)</b>						
09:00–09:20	20'	Opening Ceremony (Monterosso, B1F)				Registration & Exhibition
09:20–10:00	40'	[Plenary Session 1] Prof. Hao–Chung Kuo (Nat'l Yang Ming Chiao Tung Univ., Taiwan) "GaN Micro–LED Array for Chip–to–Chip Interconnection" (Monterosso, B1F)				
10:00–10:40	40'	[Plenary Session 2] Prof. Jun Suda (Nagoya Univ., Japan) "Vertical GaN Power Devices on GaN Substrates" (Monterosso, B1F)				
10:40–11:00	20'	Coffee Break				
11:00–12:25	85'	[MA1] Symposium GL: III–N Materials and Lighting Devices (1/7)	[MB1] Symposium GE: III–N Materials and Electronic Devices (1/7) (11:00–12:30)	[MC1] Symposium SiC: SiC Materials and Devices (1/4)		
12:25–13:45	80'	Lunch (Blue Seagull, 2F)				
13:45–15:55	130'	[MA2] Symposium GL: III–N Materials and Lighting Devices (2/7) (13:45–15:40)	[MB2] Symposium GE: III–N Materials and Electronic Devices (2/7) (13:45–16:00)	[MC2] Symposium SiC: SiC Materials and Devices (2/4) (13:45–15:50)		
15:55–16:15	20'	Coffee Break				
16:15–18:30	135'	[MA3] Symposium GL: III–N Materials and Lighting Devices (3/7)	[MB3] Symposium GE: III–N Materials and Electronic Devices (3/7)	[MC3] Symposium SiC: SiC Materials and Devices (3/4) (16:15–18:05)		
<b>October 15 (TUE)</b>						
09:00–09:40	40'	[Plenary Session 3] Prof. Bo Shen (Peking Univ., China) "Recent Progress on the Large Lattice Mis–Matched Epitaxial Growth and Defect Control of III–Nitride Semiconductors" (Monterosso, B1F)				Registration & Exhibition
09:40–10:00	20'	Coffee Break				
10:00–12:15	135'	[TA1] Special Session: BN Materials and Devices (1/3)	[TB1] Symposium GE: III–N Materials and Electronic Devices (4/7)	[TC1] Symposium SiC: SiC Materials and Devices (4/4) (10:00–11:35)		
12:15–13:35	80'	Lunch (Blue Seagull, 2F)				
13:35–15:10	95'	[TA2] Special Session: BN Materials and Devices (2/3)	[TB2] Symposium GE: III–N Materials and Electronic Devices (5/7)	[TC2] Symposium GaO: Ga <sub>2</sub> O <sub>3</sub> Materials and Electronic Devices (1/6) (13:35–15:15)	[TD1] Wide–Bandgap Semiconductor Quantum Devices 1 (13:35–15:15)	
15:10–15:30	20'	Coffee Break				
15:30–16:55	85'	[TA3] Special Session: BN Materials and Devices (3/3) (15:30–16:40)	[TB3] Symposium GE: III–N Materials and Electronic Devices (6/7) (15:30–17:00)	[TC3] Symposium GaO: Ga <sub>2</sub> O <sub>3</sub> Materials and Electronic Devices (2/6) (15:30–16:50)	[TD2] Wide–Bandgap Semiconductor Quantum Devices 2 (15:30–16:35)	
16:55–17:00	05'	Break				
17:00–18:35	95'	[TA4] Symposium GL: III–N Materials and Lighting Devices (4/7) (17:00–18:10)	[TB4] Symposium GE: III–N Materials and Electronic Devices (7/7) (17:00–18:35)	[TC4] Symposium GaO: Ga <sub>2</sub> O <sub>3</sub> Materials and Electronic Devices (3/6) (17:00–17:50)	[TD3] Novel Devices (17:00–17:45)	
<b>October 16 (WED)</b>						
09:00–10:40	100'	[WA1] Symposium GL: III–N Materials and Lighting Devices (5/7) (09:00–10:50)	[WB1] Symposium GaO: Ga <sub>2</sub> O <sub>3</sub> Materials and Electronic Devices (4/6)	[WC1] Special Session: Diamond Materials and Devices (1/3)		Registration & Exhibition
10:40–11:00	20'	Coffee Break				
11:00–12:20	80'	[WA2] Symposium GL: III–N Materials and Lighting Devices (6/7) (11:00–11:55)	[WB2] Symposium GaO: Ga <sub>2</sub> O <sub>3</sub> Materials and Electronic Devices (5/6)	[WC2] Special Session: Diamond Materials and Devices (2/3)		
12:20–13:40	80'	Lunch (Blue Seagull, 2F)				
13:40–17:00	200'	[WA3] Symposium GL: III–N Materials and Lighting Devices (7/7)	[WB3] Symposium GaO: Ga <sub>2</sub> O <sub>3</sub> Materials and Electronic Devices (6/6) (13:40–15:05)	[WC3] Special Session: Diamond Materials and Devices (3/3) (13:40–15:00)		
17:00–18:30	–	Break (Move to the Banquet Place)				
18:30–20:30	120'	Banquet (Grand Ballroom, 1F, The Westin Josun Busan)				
<b>October 17 (THU)</b>						
09:00–10:30	90'	Poster Session 1 (Vernazza, 3F) & Poster Session 2 (Forum 1, 3F)				Registration & Exhibition
10:30–10:50	20'	Coffee Break				
10:50–11:30	40'	[Plenary Session 4] Prof. Debdeep Jena (Cornell Univ., USA) "Ultrawide Bandgap Semiconductors for Power Electronics: Aluminum Nitride, Gallium Oxide, Diamond" (Monterosso, B1F)				
11:30–12:10	40'	[Plenary Session 5] CTO Samuel Cho (RFHIC, Korea) "GaN Device–Based Radio Frequency and Microwave Technology" (Monterosso, B1F)				
12:10–12:20	10'	Awards & Closing Ceremony (Monterosso, B1F)				